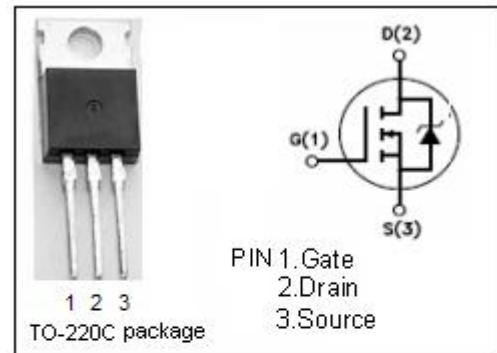


## isc N-Channel MOSFET Transistor

40N10

## • FEATURES

- Drain Current  $I_D = 40A @ T_c=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 100V$ (Min)
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 0.04 \Omega$  (Max)
- Fast Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



## • APPLICATIONS

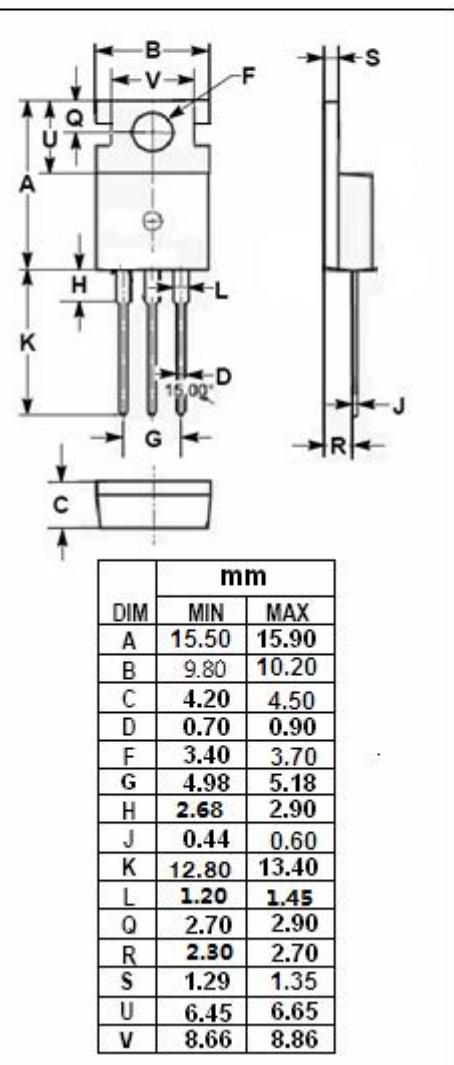
- Switching power supplies, converters, AC and DC motor controls

• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 30$	V
$I_D$	Drain Current-Continuous	40	A
$I_{DM}$	Drain Current-Single Plused	100	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	150	W
$T_j$	Max. Operating Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~150	°C

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.833	°C/W
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	°C/W



## isc N-Channel MOSFET Transistor

40N10

## • ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}= 0$ ; $I_D=250\mu\text{A}$	100			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}= V_{\text{GS}}$ ; $I_D=250\mu\text{A}$	2.0		4.0	V
$V_{\text{SD}}$	Diode Forward On-voltage	$I_S= 40\text{A}$ ; $V_{\text{GS}}= 0$			3.0	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}= 10\text{V}$ ; $I_D= 20\text{A}$			0.04	$\Omega$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}= \pm 20\text{V}$ ; $V_{\text{DS}}= 0$			$\pm 500$	nA
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=80\text{V}$ ; $V_{\text{GS}}= 0$			1	$\mu\text{A}$
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=25\text{V}$ ;			5000	pF
$C_{\text{rss}}$	Reverse Transfer capacitance	$V_{\text{GS}}=0\text{V}$ ; $f_T=1\text{MHz}$			1000	
$C_{\text{oss}}$	Output Capacitance				2500	
$t_r$	Rise Time	$V_{\text{GS}}=10\text{V}$ ;		30		ns
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$I_D=20\text{A}$ ;		17		
$t_f$	Fall Time	$V_{\text{DD}}=50\text{V}$ ;		20		
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_L=2.5\Omega$		42		

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